

# EVVOSEMI<sup>®</sup>

THINK CHANGE DO



ESD



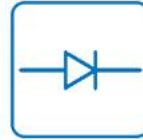
TVS



MOS



LDO



Diode



Sensor



DC-DC

## Product Specification

▶ Domestic	Part Number	IRL6372
▶ Overseas	Part Number	IRL6372
▶ Equivalent	Part Number	IRL6372

EV is the abbreviation of name EVVO

**30V N+N-Channel Enhancement Mode MOSFET**

**General Description**

The IRL6372 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R<sub>DS(ON)</sub> and gate charge for most of the small power switching and load switch applications. They meet the RoHS and Product requirement with full function reliability approved.

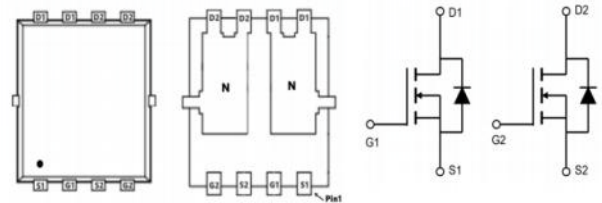
**Application**

- Battery protection
- Load switch
- Uninterruptible power supply

**General Features**

- V<sub>DS</sub> = 30V I<sub>D</sub> = 9A
- R<sub>DS(ON)</sub> < 13mΩ @ V<sub>GS</sub>=10 V
- R<sub>DS(ON)</sub> < 18mΩ @ V<sub>GS</sub>=4.5V

**SOP-8 Pin Configuration**



**Absolute Maximum Ratings (T<sub>A</sub>=25 °C unless otherwise noted)**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	9	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	8.2	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6.5	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	5.6	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	30	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	15	mJ
I <sub>AS</sub>	Avalanche Current	22	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	1.6	W
P <sub>D</sub> @T <sub>A</sub> =70°C	Total Power Dissipation <sup>4</sup>	1.0	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	75	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction Case <sup>1</sup>	4.8	°C/W

**30V N+N-Channel Enhancement Mode MOSFET**
**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25 °C, I <sub>D</sub> =1mA	---	0.023	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	---	---	13	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	---	18	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.08	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25 °C	---	---	1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55 °C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =15A	---	32	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.7	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =12A	---	5.3	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	0.78	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =1.5□ I <sub>D</sub> =20A	---	6.4	---	ns
T <sub>r</sub>	Rise Time		---	39	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	21	---	
T <sub>f</sub>	Fall Time		---	4.7	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	580	---	pF
C <sub>oss</sub>	Output Capacitance		---	97	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	39	---	
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	37	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	75	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25 °C	---	---	1	V

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=22A
4. The power dissipation is limited by 175 °C junction temperature
5. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



30V N+N-Channel Enhancement Mode MOSFET

Typical Characteristics

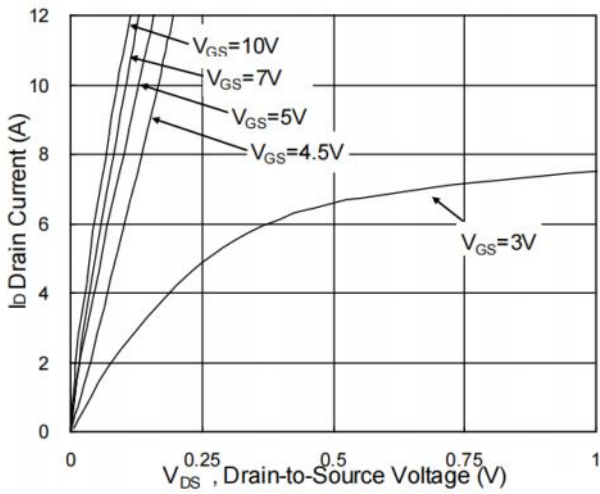


Fig.1 Typical Output Characteristics

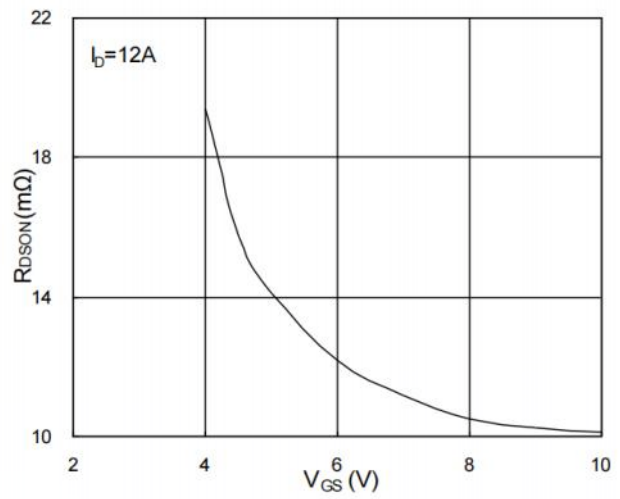


Fig.2 On-Resistance vs. G-S Voltage

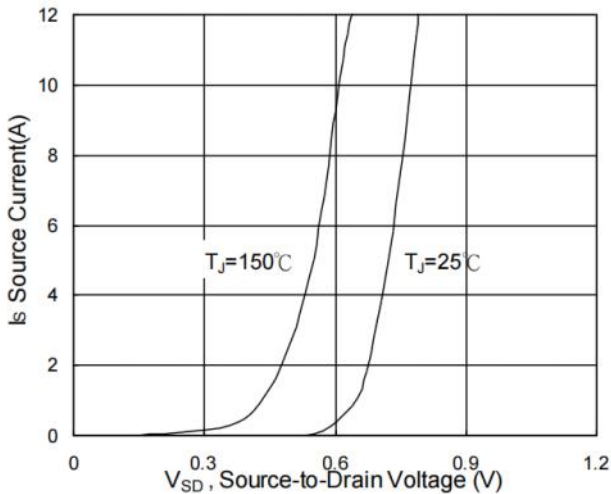


Fig.3 Forward Characteristics of Reverse

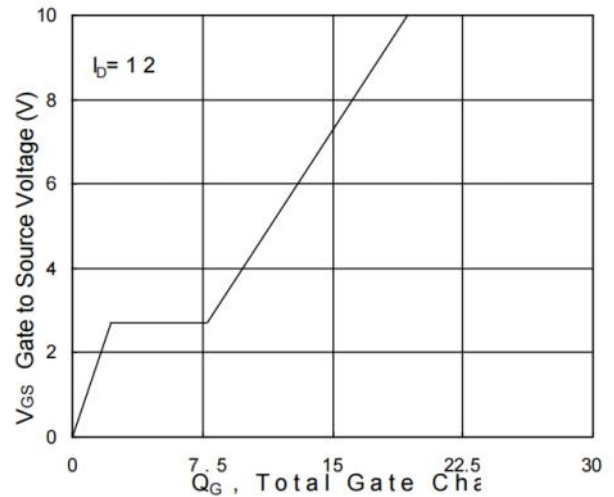


Fig.4 Gate-charge Characteristics

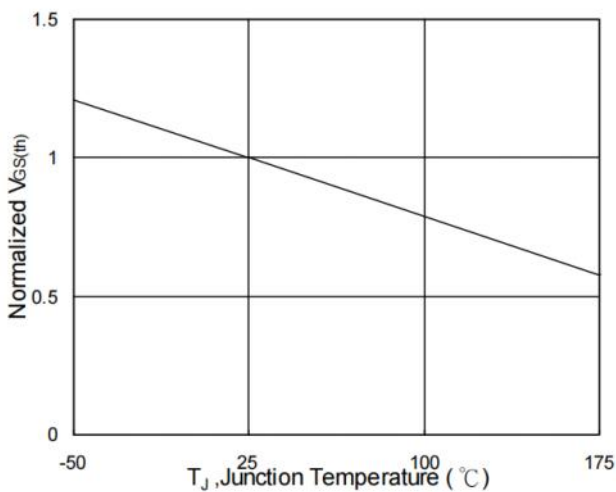


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

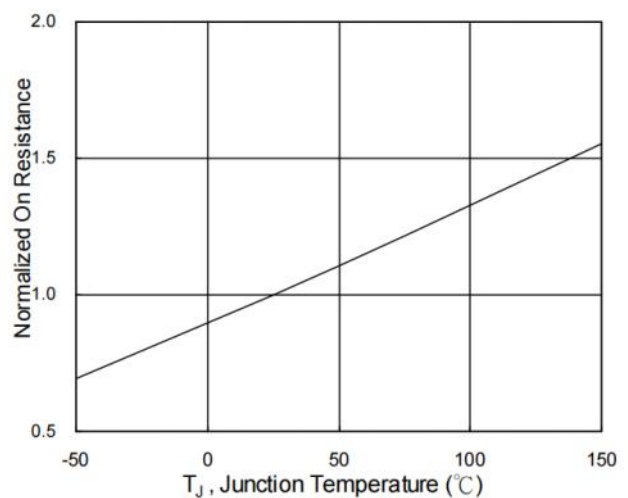


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$

30V N+N-Channel Enhancement Mode MOSFET

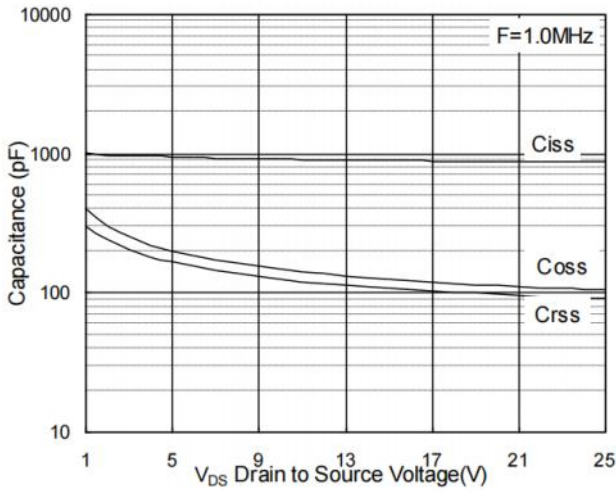


Fig.7 Capacitance

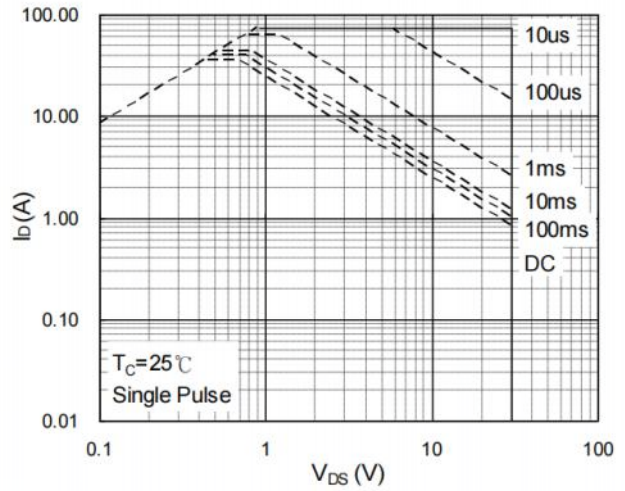


Fig.8 Safe Operating Area

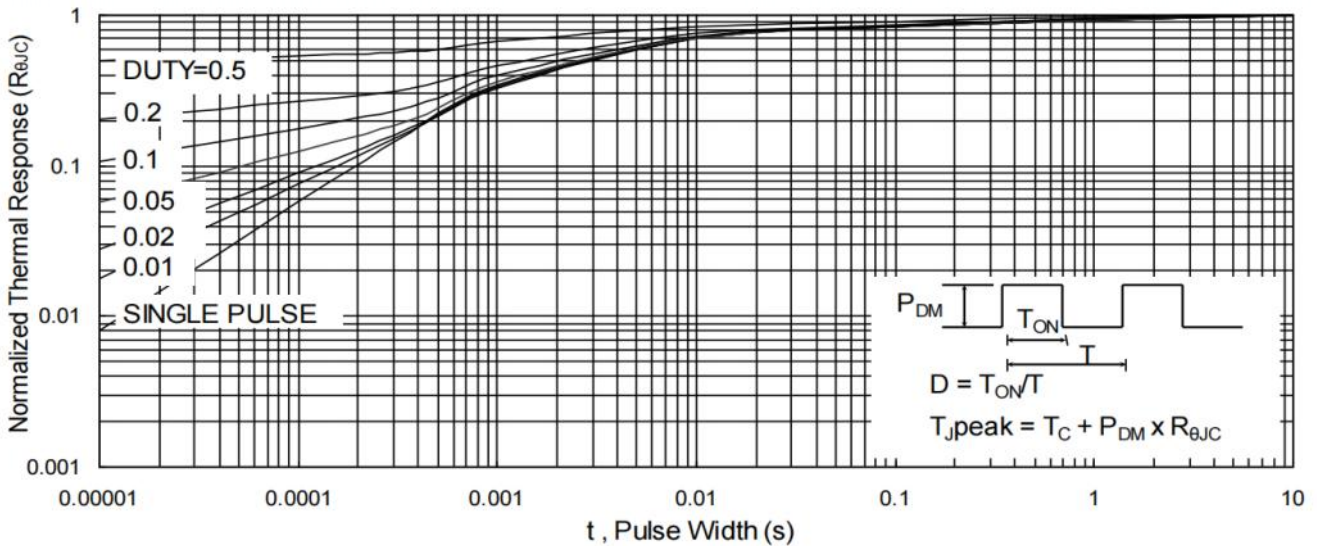


Fig.9 Normalized Maximum Transient Thermal Impedance

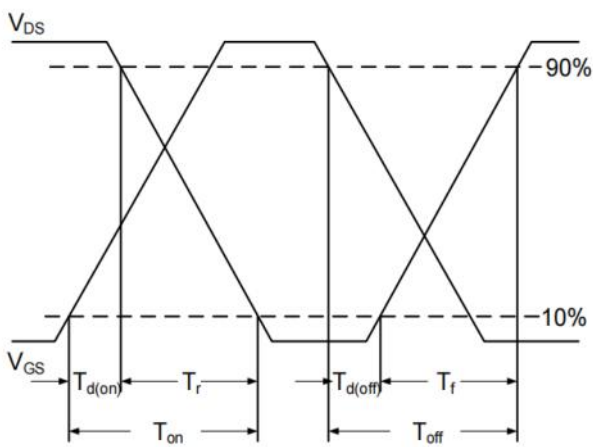


Fig.10 Switching Time Waveform

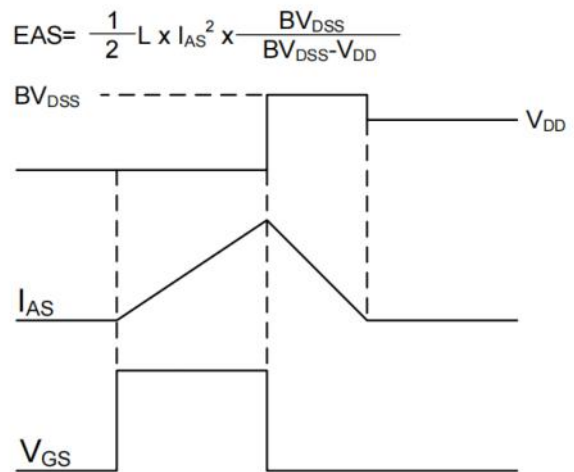
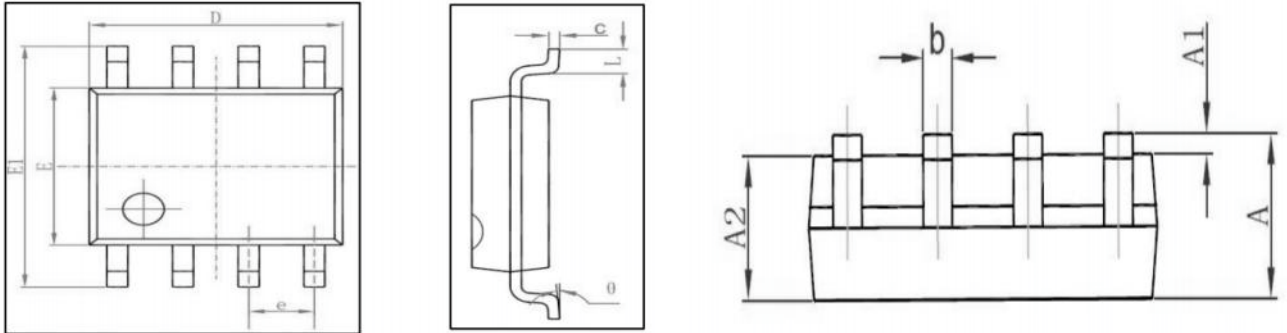


Fig.11 Unclamped Inductive Waveform

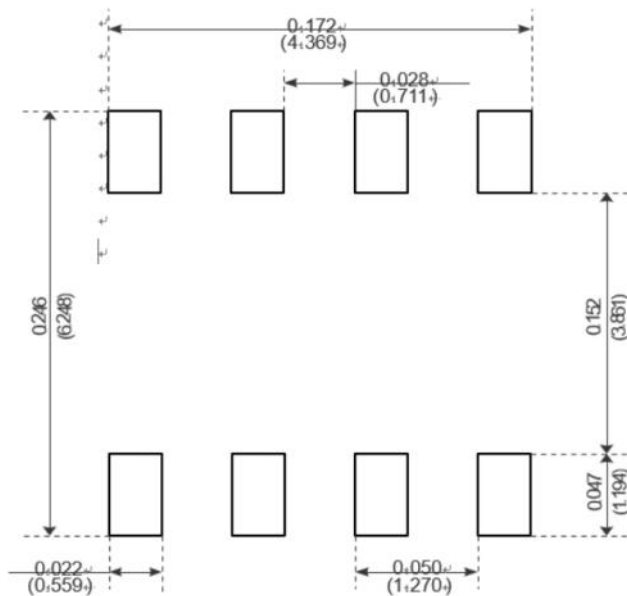
$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

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**Package Mechanical Data-SOP-8**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads



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